

NTJD4001N

Small Signal MOSFET

30 V, 250 mA, Dual N-Channel, SC-88



ON Semiconductor®

Features

- Low Gate Charge for Fast Switching
- Small Footprint - 30% Smaller than TSOP-6
- ESD Protected Gate
- Pb-Free Package is Available

Applications

- Low Side Load Switch
- Li-Ion Battery Supplied Devices - Cell Phones, PDAs, DSC
- Buck Converters
- Level Shifts

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

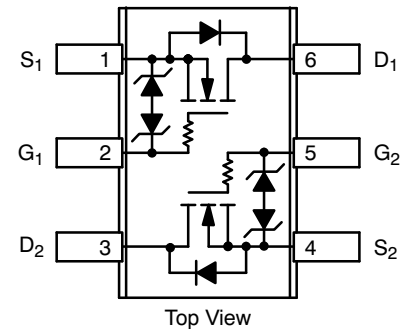
Parameter		Symbol	Value	Units	
Drain-to-Source Voltage		V _{DSS}	30	V	
Gate-to-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current (Note 1)	Steady State	I _D	T _A = 25 °C	250	mA
			T _A = 85 °C	180	
Power Dissipation (Note 1)	Steady State	T _A = 25 °C	P _D	272	mW
Pulsed Drain Current		t = 10 μs	I _{DM}	600	mA
Operating Junction and Storage Temperature		T _J , T _{STG}	-55 to 150		°C
Source Current (Body Diode)		I _S	250		mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

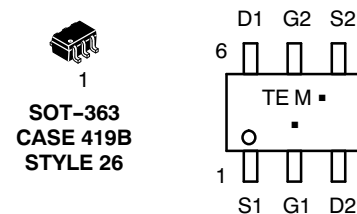
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

V _{(BR)DSS}	R _{DS(on)} TYP	I _D Max
30 V	1.0 Ω @ 4.0 V	250 mA
	1.5 Ω @ 2.5 V	

SOT-363 SC-88 (6 LEADS)



MARKING DIAGRAM & PIN ASSIGNMENT



TE = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTJD4001NT1	SOT-363	3000/Tape & Reel
NTJD4001NT1G	SOT-363 (Pb-Free)	3000/Tape & Reel
NTJD4001NT2G	SOT-363 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 100 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			56		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 30 V			1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10 V			±1.0	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 100 μA	0.8	1.2	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-3.2		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.0 V, I _D = 10 mA		1.0	1.5	Ω
		V _{GS} = 2.5 V, I _D = 10 mA		1.5	2.5	
Forward Transconductance	g _{FS}	V _{DS} = 3.0 V, I _D = 10 mA		80		mS

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 5.0 V		20	33	pF
Output Capacitance	C _{OSS}			19	32	
Reverse Transfer Capacitance	C _{RSS}			7.25	12	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 5.0 V, V _{DS} = 24 V, I _D = 0.1 A		0.9	1.3	nC
Threshold Gate Charge	Q _{G(TH)}			0.2		
Gate-to-Source Charge	Q _{GS}			0.3		
Gate-to-Drain Charge	Q _{GD}			0.2		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 5.0 V, I _D = 10 mA, R _G = 50 Ω		17		ns
Rise Time	t _r			23		
Turn-Off Delay Time	t _{d(OFF)}			94		
Fall Time	t _f			82		

DRAIN-SOURCE DIODE CHARACTERISTICS

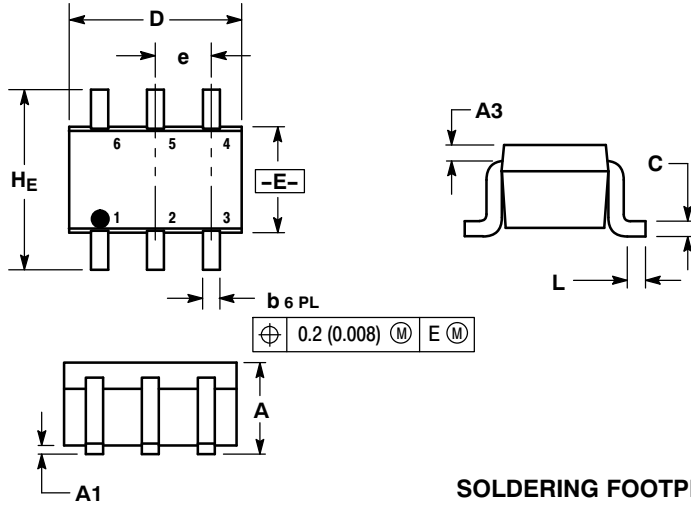
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 mA	T _J = 25°C	0.65	0.7	V
			T _J = 125°C	0.45		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, di _S /dt = 8.0 A/μs, I _S = 10 mA		12.4		ns

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

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PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W



NOTES:

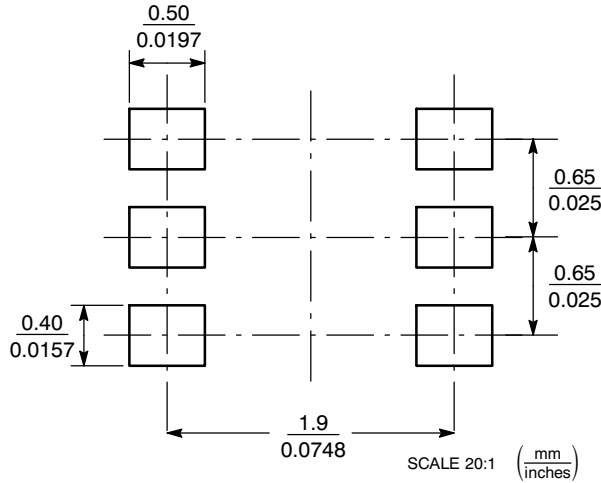
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 26:

- PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.